

DIALOG(R)File 351:Derwent WPI
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Aluminium nitride powder used as filler for semiconductor sealing - has
aluminium nitride particles bonded to a silanol group content
polyorganosiloxane film through a Al-O-Si group
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JP 11116213	A	19990427	JP 97282390	A	19971015	199927 B

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Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
JP 11116213	A		9	C01B-021/072	

Abstract (Basic): JP 11116213 A

NOVELTY - The powder has aluminium nitride (AlN) particles bonded to a silanol group content polyorganosiloxane film through a Al-O-Si group. DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for the manufacture of aluminium nitride powder. Silanol group content polyorganosiloxane was mixed with an organic solvent to form a coating solution. The solution was applied on the AlN particles and condensation of the Al-OH group and silanol group is carried out to form Al-O-Si bonding.

USE - Used as filler for semiconductor sealing.

ADVANTAGE - The powder excels in water resistance and heat conductivity. A polyorganosiloxane film of high strength and low peelability is provided on the powder. The powder is inexpensive.

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Derwent Class: A60; E33; G01; L03

International Patent Class (Main): C01B-021/072

International Patent Class (Additional): C08K-009/06